Wednesday 23.10: Uranienborg Church

2000-2100 Organ concert by Wolfgang Skorupa

Thursday 24.10: Forskningsparken (Oslo Science Park), Auditorium Forum

0830-0900 Registration and morning coffee

Chair: C. Jagadish, Australian National University, Australia

0900-0910 Opening remarks

0910-0940 Arne Nylandsted Larsen, Aarhus University, Denmark
In-growth of an electrically active defect in high-purity silicon after proton irradiation

0940-1010 Jose Coutinho, University of Aveiro, Portugal
What have we learned about vacancy reaction products in silicon from first-principles modeling and DLTS joint studies

1010-1040 Jim Williams, Australian National University, Australia
Enhancing silicon's optical properties by controlled introduction of defect and impurity levels

1040-1100 Coffee Break

Chair: Anders Hallén, KTH Royal Institute of Technology, Sweden

1100-1130 Roberta Nipoti, CNR-IMM, Bologna, Italy
Heavy p-type doping of Al^+ implanted 4H-SiC

1130-1200 Eric Janzén, Linköping University, Sweden
Isotopic Control for Ultimate Material Properties of SiC

1200-1230 Jean Francois Barbot, CNRS - Université de Poitiers, France
Strain/defect accumulation in implanted SiC

1230-1250 Giovanni Alfieri, Kyoto University, Japan
Electrical characterization of majority and minority carriers in p-type 4H-SiC

1250-1345 Lunch

Chair: Augustinas Galeckas, University of Oslo, Norway

1345-1415 Anders Hallén, KTH Royal Institute of Technology, Sweden
Radiation induced defects in SiC bulk and interfaces

1415-1445 Margareta K. Linnarsson, KTH Royal Institute of Technology, Sweden
Diffusion of hydrogen and alkali metals in silicon carbide

1445-1515 Nguyen T. Son, Linköping University, Sweden
The carbon vacancy in SiC

1515-1555 Break

Chair: Arne Nylandsted Larsen, Aarhus University, Denmark

1555-1625 Wolfgang Skorupa, Helmholtz-Zentrum Dresden-Rossendorf, Germany
Short time thermal processing and defects: history and ideology

1625-1655 Joachim Grillenberger, Paul Scherrer Institute Villigen, Switzerland
The High Intensity Proton Accelerator of the Paul Scherrer Institute

1655-1725 Ulrike Grossner, ABB Corporate Research, Switzerland
Defect science for real-world products

1725-1755 Ioana Pintilie, Natl Inst Mat Phys, Bucharest, Romania
Bridging the gap between defect analysis and device characteristics

1800-1900 Poster Session; see list at the end of the program
*The Poster Session will be held in **MiNa-Lab***

1930- Symposium Dinner at "Lofoten Fiskerestaurant"

Friday 25.10, Forskningsparken (Oslo Science Park), Auditorium Forum

Chair: Edouard V. Monakhov, University of Oslo, Norway

0900-0930 Tony Peaker, University of Manchester, UK
Using Laplace High Resolution DLTS to Understand Defects and Recombination in Solar Silicon

0930-1000 Vladimir. P. Markevich, University of Manchester, UK
Trivacancy and trivacancy-oxygen defects in silicon

1000-1030 Leonid Murin, NAS of Belarus, Belarus
Oxygen-related defects in silicon: Local vibrational mode characterization

1030-1100 Break

Chair: Jim Williams, Australian National University, Australia

1100-1130 Jan Linnros, KTH Royal Institute of Technology, Sweden
Single dot spectroscopy of silicon quantum dots

1130-1200 Vittorio Privitera, CNR IMM, Catania, Italy
Twenty years of ions, defects, diffusion and water

1200-1230 Antonino La Magna, CNR IMM, Catania, Italy
The Scandinavian School's contribution to the theoretical understanding of the non-equilibrium kinetics in Si

1230-1330 Lunch

Chair: Lasse Vines, University of Oslo, Norway

1330-1400 Dominique Mangelinck, IM2NP, CNRS/Aix-Marseille Université, France
Diffusion and growth in silicide for advanced MOS structures

1400-1420 Andrej Kuznetsov, University of Oslo, Norway
Impurity Sublattice Localization in ZnO Revealed by Li Marker Diffusion

1420-1440 Clas Persson, University of Oslo, Norway
Nanostructured ZnO-X with tailored optoelectronic properties

1440-1500 Break

1500-1520 Lucia Romano, CNR-IMM MATIS and, Università di Catania, Italy
Nanoporous Ge induced by ion implantation: formation mechanism, properties and novel applications

1520-1550 C. Jagadish, Australian National University, Australia
III-V Semiconductor Nanowires for Optoelectronics and Energy Applications

1550-1600 Closing remarks

Poster Session

P1: K.M.Johansen, L. Vines, T.S. Bjørheim, R. Schifano and B.G. Svensson
A diffusion model case study: Al in Single crystalline Zinc Oxide

P2: Tor S. Bjørheim, K.M. Johansen and T. Norby
Defect structure of ZnO from first principles calculations

P3: C. Modanese, L. Arnberg, M. Di Sabatino
Temperature-dependent majority carrier mobility in compensated silicon for solar cells

P4: H. N. Riise, R. Schifano, A. Azarov and B.G. Svensson
Annealing of Si-doped and Al-doped ZnO thin films

P5: P. Lindberg, K. Bergum, B.G. Svensson, E.V. Monakhov
ZnO:Al on n-type Si(100), (110) and (111): Electronic properties of the interface

P6: H.M. Ayedh, V. Bobal, R. Nipoti, A. Hallén and B.G. Svensson
Formation of carbon vacancy during high-temperature treatment of 4H silicon carbide

P7: V. Quemener, L. Vines, E. V. Monakhov and B. G. Svensson
Intrinsic and impurity related defects in ZnO.

P8: C. Bhoodoo, L. Vines, E.V. Monakhov and B.G. Svensson
Dopant concentration dependence of local compensation in low-dose ion-bombarded n-type Silicon

P9: Alexander Hupfer, University of Oslo, Norway
Influence of hydrogen on the E3 generation in Proton Implanted hydrothermally grown Zinc Oxide

P10: L. Vines, K.M. Johansen, and B.G. Svensson
Diffusion of ion implanted elements in ZnO

P11: N. Ganagona, L.Vines, E.V. Monakhov and B.G. Svensson
Hydrogen related defects in proton implanted Cz Silicon

P12: N. Malik, K. Schjølberg-Henriksen, E. Poppe and T.G. Finstad
Al-Al Thermocompression Bonding for Wafer-Level MEMS Packaging

P13: A. Yu. Azarov, P. Rauwel, L. Vines, A. Yu. Kuznetsov, and B. G. Svensson
Annealing of ZnO implanted with Ag: defect evolution and dopant distribution

P14: F. Herklotz, K.M. Johanson, B.G. Svensson
Thermal stability of acceptor-hydrogen complexes in ZnO

P15: S. Zh. Karazhanov, M. Ganchenkova, and E. S. Marstein
Structural properties of and vibrational zero point energy for H-doped Silicon

P16: A. Galeckas, V. Venkatachalapathy, A. Yu. Azarov, M. Trunk, and A. Yu. Kuznetsov
Carrier dynamics in graded bandgap ZnCdxO structures

P17: R. Scifano
Role of dopants in ZnO for photovoltaics applications